

Low $V_{CE(sat)}$ Transistor ($-20V$, $-3A$)

2SB1424 / 2SA1585S

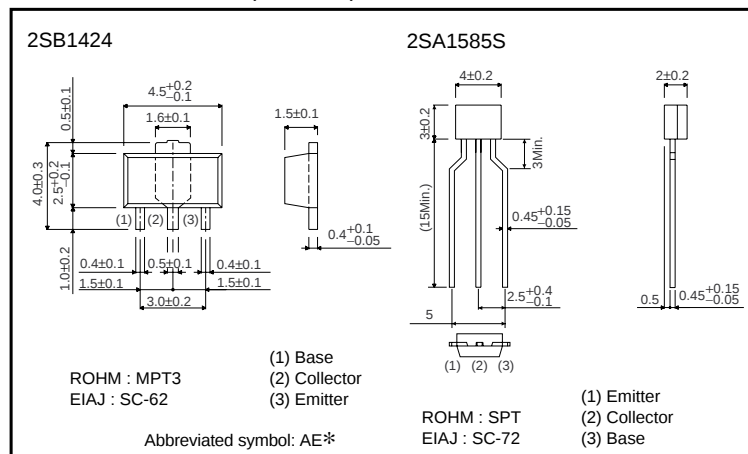
●Features

- 1) Low $V_{CE(sat)}$.
 $V_{CE(sat)} = -0.2V$ (Typ.)
 $(I_C/I_B = -2A / -0.1A)$
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD2150 / 2SC4115S.

●Structure

Epitaxial planar type
 PNP silicon transistor

●External dimensions (Unit : mm)



* Denotes h_{FE}

●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	2SB1424	I_C	-3
	2SA1585S	I_C	-2
		I_{CP}	-5
			A(Pulse) *
Collector power dissipation	2SB1424	P_C	0.5
	2SA1585S	P_C	0.4
			W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to 150	$^\circ C$

* Single pulse $P_W=10ms$

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-20	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-20	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	$I_E = -50\mu A$
Collector cutoff current	I_{CBO}	-	-	-0.1	μA	$V_{CB} = -20V$
Emitter cutoff current	I_{EBO}	-	-	-0.1	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_C/I_B = -2A/-0.1A$
DC current transfer ratio	h_{FE}	120	-	390	-	$V_{CE} = -2V, I_C = -0.1A$
Transition frequency	f_T	-	240	-	MHz	$V_{CE} = -2V, I_E = 0.5A, f = 100MHz$
Output capacitance	C_{ob}	-	35	-	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

●Packaging specifications and h_{FE}

Type	h_{FE}	Package	Taping	
		Code	TP	T100
		Basic ordering unit (pieces)	5000	1000
2SA1585S	QR		○	-
2SB1424	QR		-	○

 h_{FE} values are classified as follows :

Item	Q	R
h_{FE}	120 to 270	180 to 390

●Electrical characteristic curves

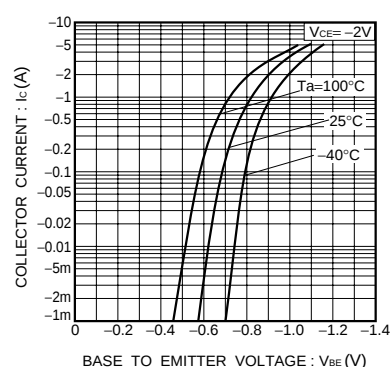


Fig.1 Grounded emitter propagation characteristics

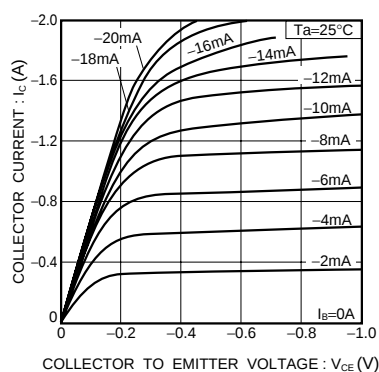


Fig.2 Grounded emitter output characteristics (I)

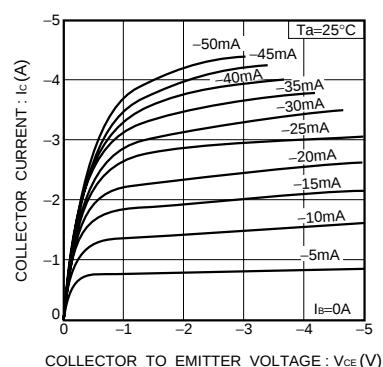


Fig.3 Grounded emitter output characteristics (II)

Transistors

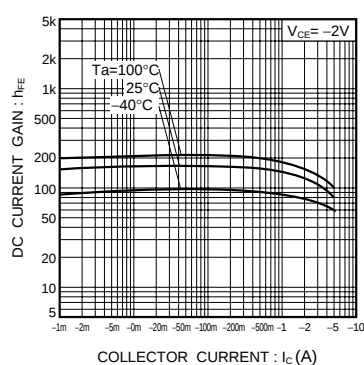


Fig.4 DC current gain vs. collector current

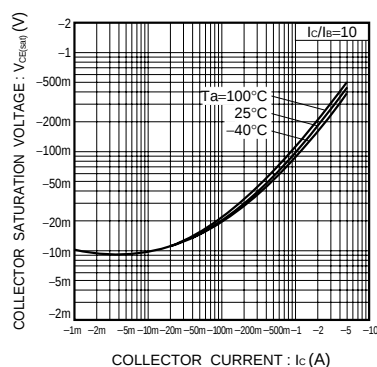


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

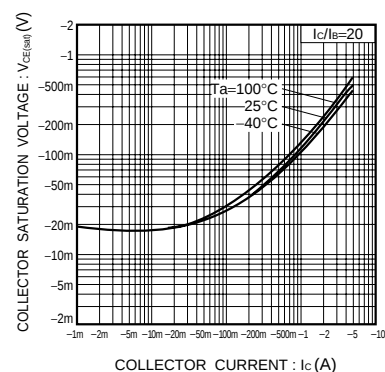


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

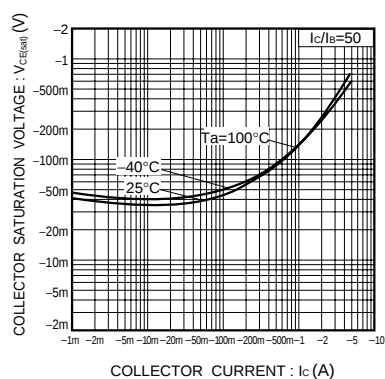


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

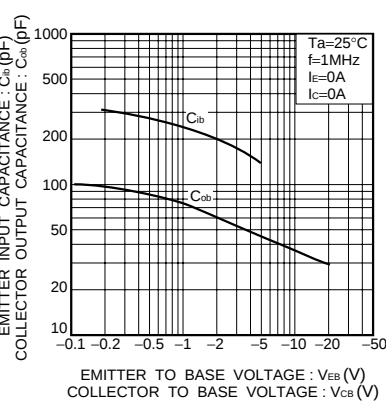
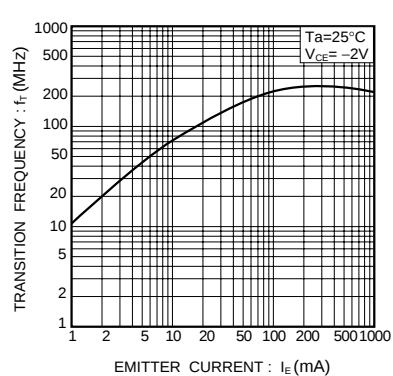
Fig.8 Gain bandwidth product vs. emitter current
Collector output capacitance vs. collector-base voltage

Fig.9 Emitter input capacitance vs. emitter base voltage

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